

## Diffusion Furnace

Phosphorous Diffusion is widely used in manufacture of solar cells. Silicon wafers are doped with small amounts of phosphorous to create the n-junction of the solar cell. This process is accomplished by depositing phosphorous vapor or coating on top of a silicon substrate. It is then fired at temperatures between 800°C and 1000°C to drive the phosphorous into the silicon, thus creating the n-junction

### Features

- In-Line Diffusion Furnace
  - The system can be configured to process up to 1,500 wafers per hour providing uniform and repeatable emitters

### Applications

### Specifications

- Silicon wafers are coated with a phosphoric acid solution and diffused in a quartz-lined continuous furnace between 850 and 900°C

### CE Compliance

- This option is for the design and manufacture of the furnace evaluated to the requirements of the Machinery Directive (2006/42/EC) and Electromagnetic Compatibility (EMC) Directive (2004/108/EC). Our company offers self compliance to the Directives and the applicable harmonized standards. This



